

## **DME 150**

150 Watts, 50 Volts, Pulsed Avionics 1025 - 1150 MHz

<b>GENERAL DESCRIPTION</b> The DME 150 is a high power COMMON BA designed for pulsed systems in the frequency b device has gold thin-film metallization and diff highest MTTF. The transistor includes input a broadband capabilit. Low thermal resistance p temperature, extends life. <b>ABSOLUTE MAXIMUM R</b>	SE bipolar transistor. It is and 1025-1150 MHz. The fused ballasting for proven nd ouput prematch for ackage reduces junction	CASE OUTLINE 55AY, STYLE 1
Maximum Power Dissipation @ 25°C <sup>2</sup>	290 Watts	
Maximum Voltage and Current		
BVces Collector to Base Voltage	55 Volts	
BVebo Emitter to Base Voltage	4.0 Volts	
Ic Collector Current	15 Amps	
Maximum Temperatures	-	
Storage Temperature	$-65 \text{ to} + 150^{\circ} \text{C}$	
Operating Junction Temperature	$+ 150^{\circ}C$	
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## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η <sub>c</sub> VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 1025-1150  MHz Vcc = 50 Volts PW = 10 $\mu$ sec DF = 1% F = 1025 MHz	150 7.8	8.3 40	25 20:1	Watts Watts dB %

BVebo BVces h <sub>FE</sub> θjc <sup>2</sup>	Emitter to Base Breakdown Collector to Emitter Breakdown DC - Current Gain Thermal Resistance	Ie = 15 mA Ic = 25 mA Ic = 250 mA, Vce = 5 V	4.0 55 20		100 0.6	Volts Volts °C/W
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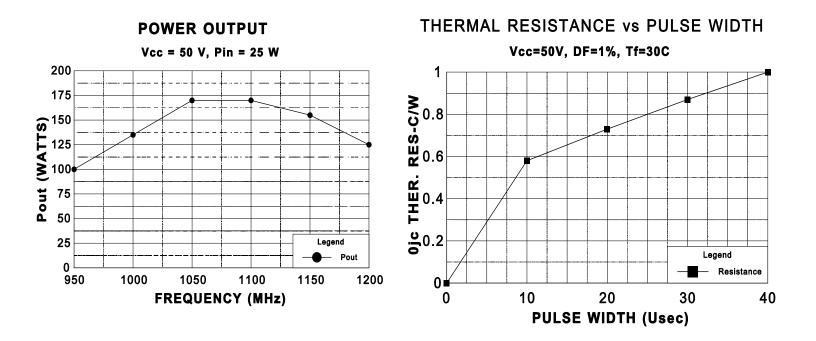
Note 1: At rated output power and pulse conditions

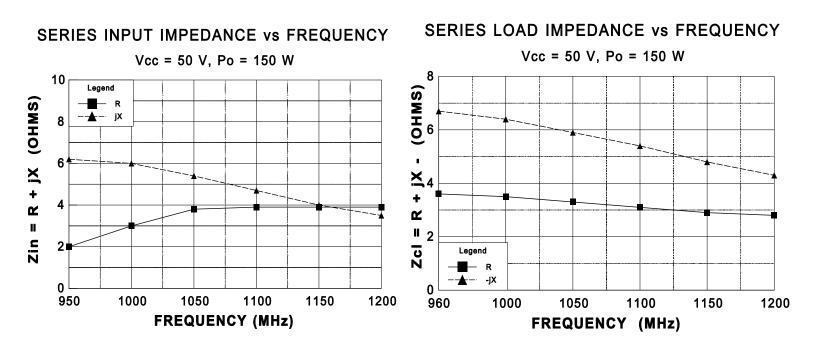
2: At rated pulse conditions

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